



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > -60V$
- $I_C = -4A$ Continuous Collector Current
- Low Saturation Voltage $V_{CE(sat)} < -75mV @ 1A$
- $R_{CE(sat)} = 45m\Omega$
- h_{FE} Characterised up to 4A
- High h_{FE} Min 160 @ 1A
- 1.5W Power Dissipation
- Complementary NPN type: NK-ZXTN19060CFF

Mechanical Data

- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.012 grams (Approximate)

Description

This medium voltage PNP transistor is designed for applications requiring high-gain and low-saturation voltage. The SOT23F package is PIN compatible with the industry standard SOT23 footprint while offering a lower profile and higher power dissipation for applications where power density is of utmost importance.

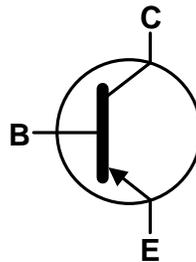
Applications

- High-Side Driver
- Motor Drive
- Load Disconnect Switch

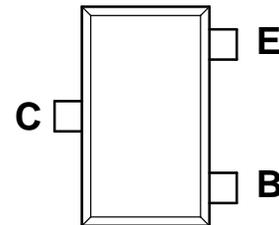


SOT23F

Top View



Device Symbol



Top View
Pin Configuration

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Collector Voltage (Reverse Blocking)	V_{ECO}	-7	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-4	A
Peak Pulse Current	I_{CM}	-7	A
Base Current	I_B	-1	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

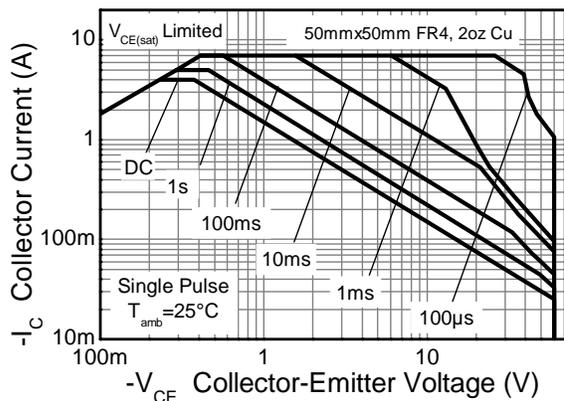
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P_D	0.84	W mW/°C
		6.72	
		1.34	
		10.72	
		1.50	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	12.0	°C/W
		2.0	
		16.0	
		149	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	93	°C/W
		83	
		60	
		43.77	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 10)

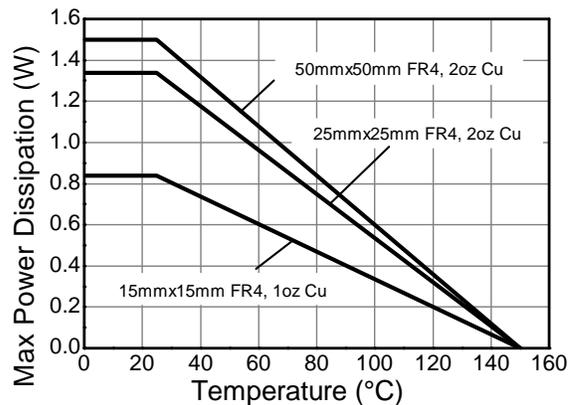
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 - Same as Note 7, whilst measured at $t < 5$ seconds.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

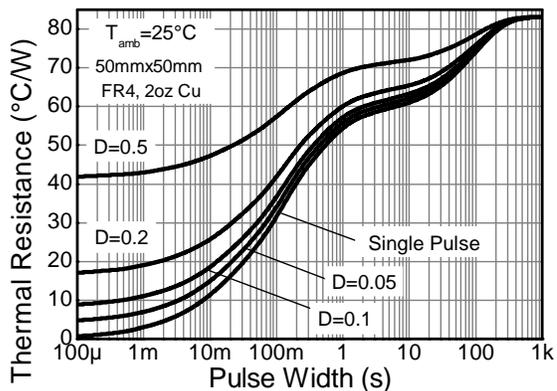
Thermal Characteristics and Derating Information



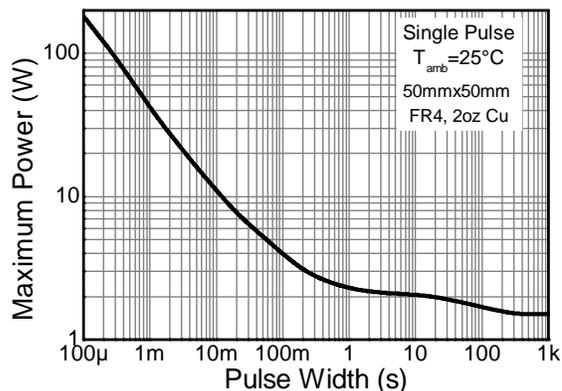
Safe Operating Area



Derating Curve



Transient Thermal Impedance



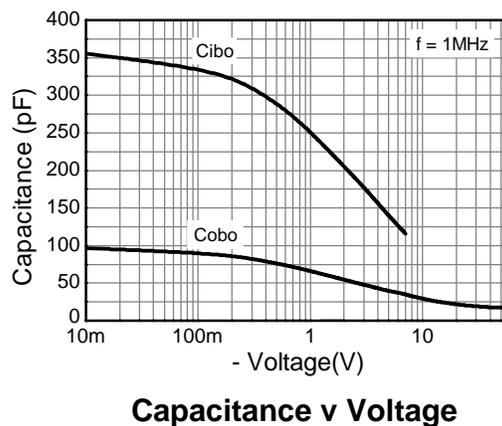
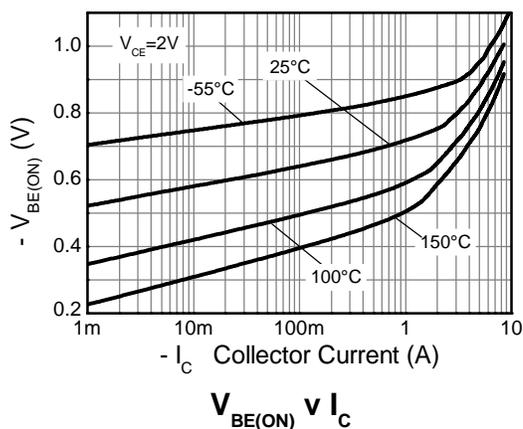
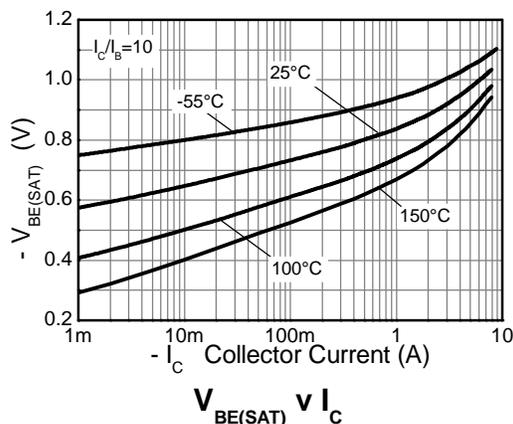
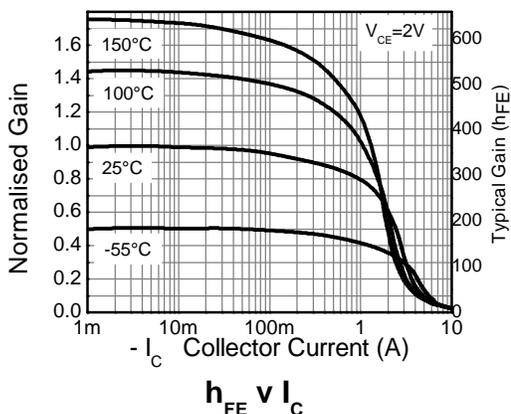
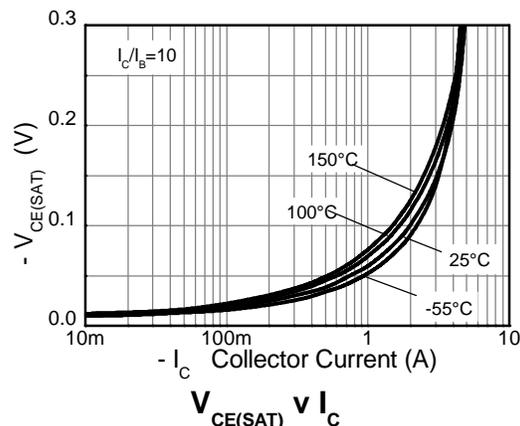
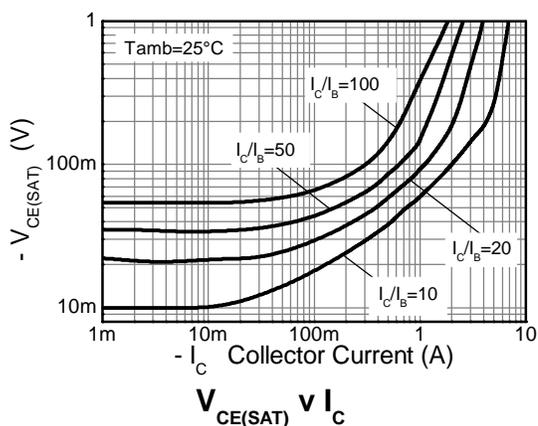
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-60	-110	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	-60	-90	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.4	—	V	I _E = -100μA
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	-7	-8.4	—	V	I _E = -100μA; R _{BC} < 1kΩ or 0.25V < V _{BC} < -0.25V
Emitter-Collector Breakdown Voltage (base open)	BV _{ECO}	-7	-8.8	—	V	I _E = -100μA
Collector-Base Cut-Off Current	I _{CBO}	—	<-1	-50	nA	V _{CB} = -60V
Emitter-Base Cut-Off Current	I _{EBO}	—	<-1	-50	nA	V _{CB} = -60V, T _A = +100°C
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h _{FE}	200 160 30	350 280 50	500 — —	—	I _C = -100mA, V _{CE} = -2V I _C = -1A, V _{CE} = -2V I _C = -4A, V _{CE} = -2V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-60 -140 -180	-75 -200 -270	mV	I _C = -1A, I _B = -100mA I _C = -1A, I _B = -20mA I _C = -4A, I _B = -400mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	-935	-1,050	mV	I _C = -4A, I _B = -400mA
Base-Emitter On Voltage	V _{BE(on)}	—	-835	-950	mV	I _C = -4A, V _{CE} = -2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	—	180	—	MHz	I _C = -50mA, V _{CE} = -10V, f = 50MHz
Output Capacitance	C _{obo}	—	29.5	40	pF	V _{CB} = -10V, f = 1MHz
Delay Time	t _d	—	24.3	—	ns	V _{CC} = -10V, I _C = -500mA, I _{B1} = -I _{B2} = -50mA
Rise Time	t _r	—	13.2	—	ns	
Storage Time	t _s	—	456	—	ns	
Fall Time	t _f	—	68.2	—	ns	

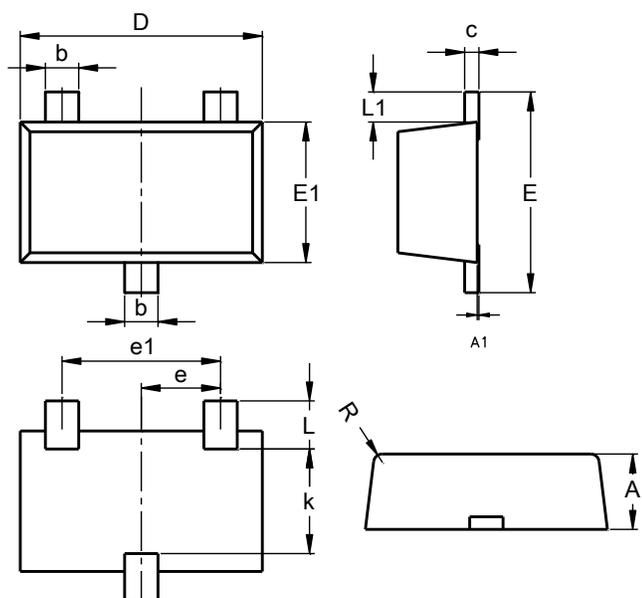
Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

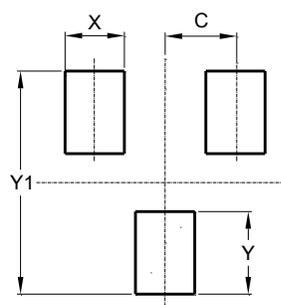
SOT23F



SOT23F			
Dim	Min	Max	Typ
A	0.80	1.00	0.90
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	0.190 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

Suggested Pad Layout

SOT23F



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000